

SANYO

No.3099

2SC4493

NPN Triple Diffused Planar Silicon Transistor

High-Voltage Amp,
High-Voltage Switching Applications**Features**

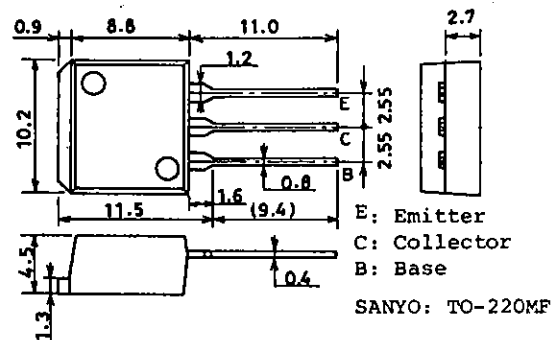
- High breakdown voltage
- Small c_{ob}
- High reliability (adoption of HVP process)
- Intended for high-density mounting (Suitable for sets whose height is restricted)

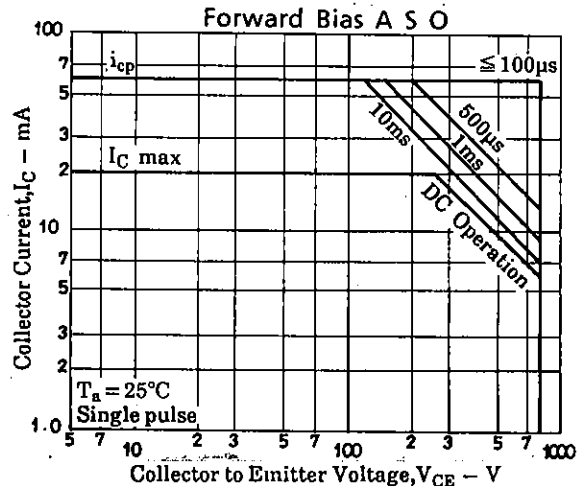
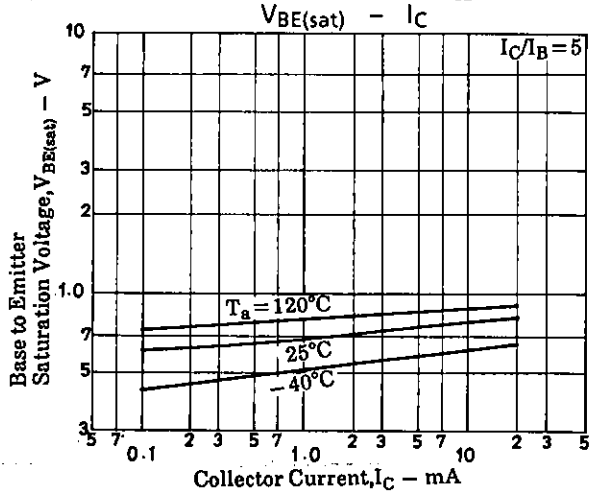
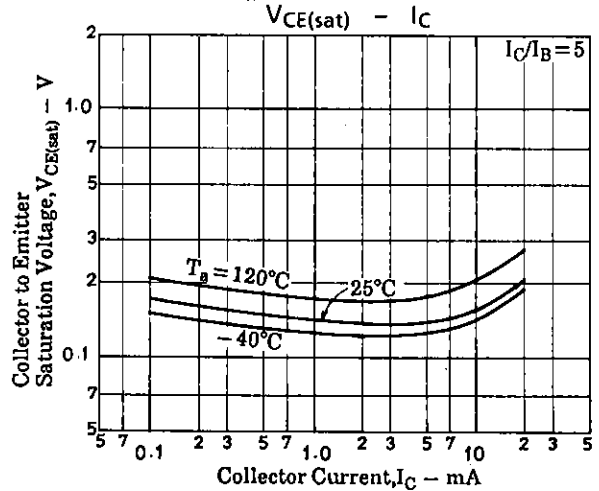
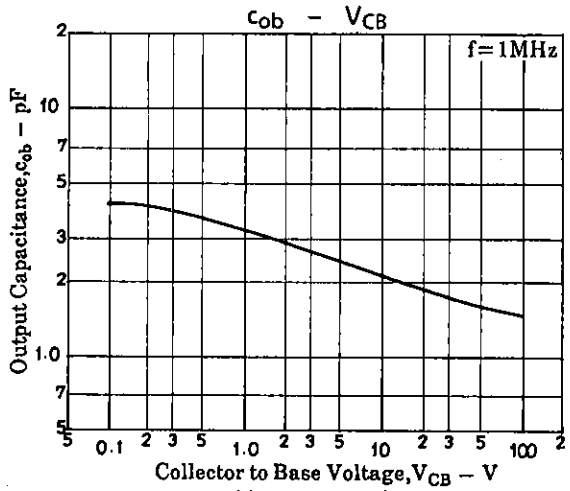
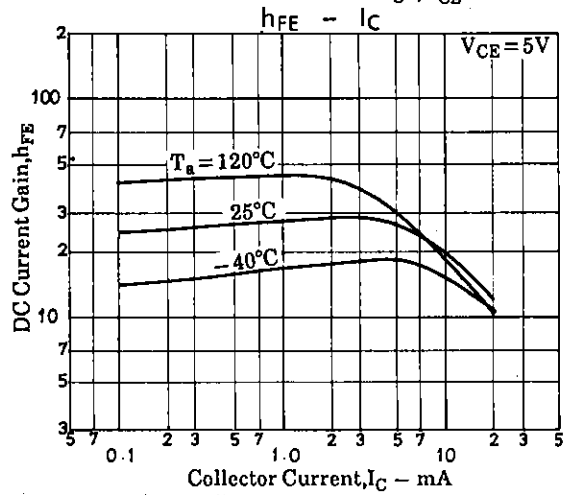
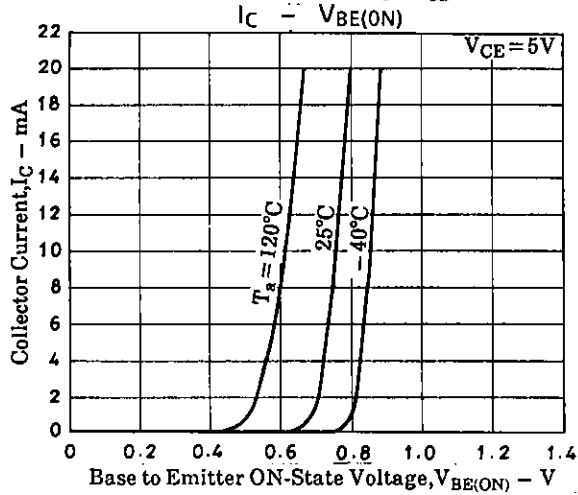
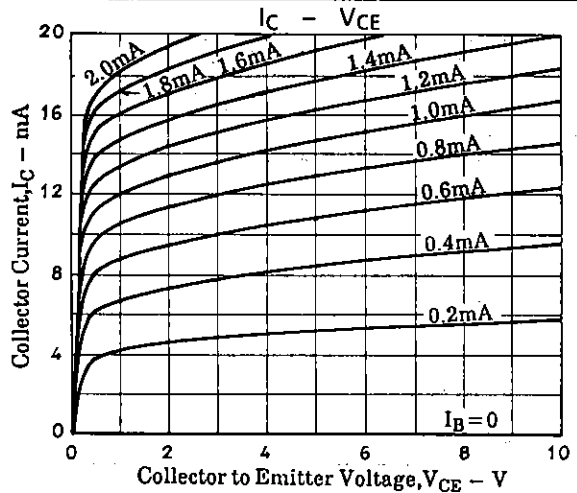
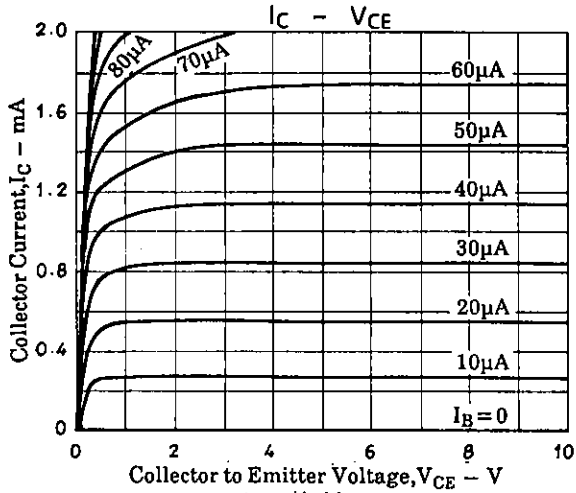
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

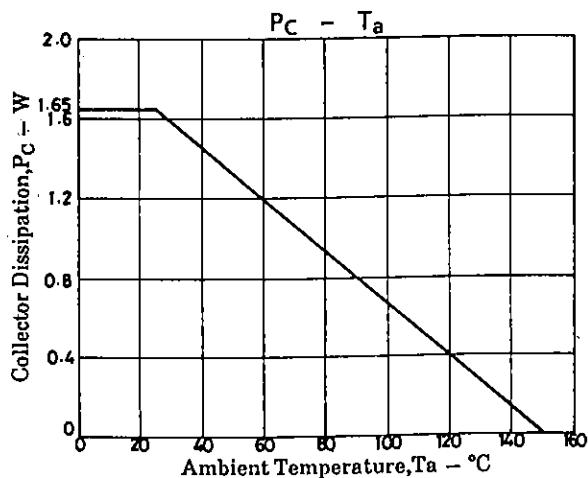
			unit
Collector to Base Voltage	V_{CBO}	800	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current	I_C	20	mA
Peak Collector Current	i_{cp}	60	mA
Collector Dissipation	P_C	1.65	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	20		50	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	10			
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 2\text{mA}$		40		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	800			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	7			V
Output Capacitance	c_{ob}	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		1.6		pF

Package Dimensions 2049B
(unit: mm)





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